

16M-BIT CMOS FAST SRAM 16M-WORD BY 1-BIT

Description

The μPD4416001 is a high speed, low power, 16,777,216 bits (16,777,216 words by 1 bits) CMOS static RAM.

Operating supply voltage is 3.3 V $\pm$ 0.3 V (A version) or 2.5 V $\pm$ 0.125 V (C version).

The μPD4416001 is packaged in a 54-pin plastic TSOP (II).

Features

- 16,777,216 words by 1 bits
- Fast access time : 12, 15 ns (MAX.)
- Output Enable input for easy application

Ordering Information

Part number	Package	Supply voltage	Access time (MAX.)	Supply current (MAX.)	
				At operating	At standby
μPD4416001G5-A12-9JF	54-pin plastic TSOP (II) (400 mil) (Normal bent)	3.3 V $\pm$ 0.3 V	12 ns	190 mA	10 mA
μPD4416001G5-A15-9JF			15 ns	150 mA	
μPD4416001G5-C12-9JF		2.5 V $\pm$ 0.125 V	12 ns	190 mA	
μPD4416001G5-C15-9JF			15 ns	150 mA	

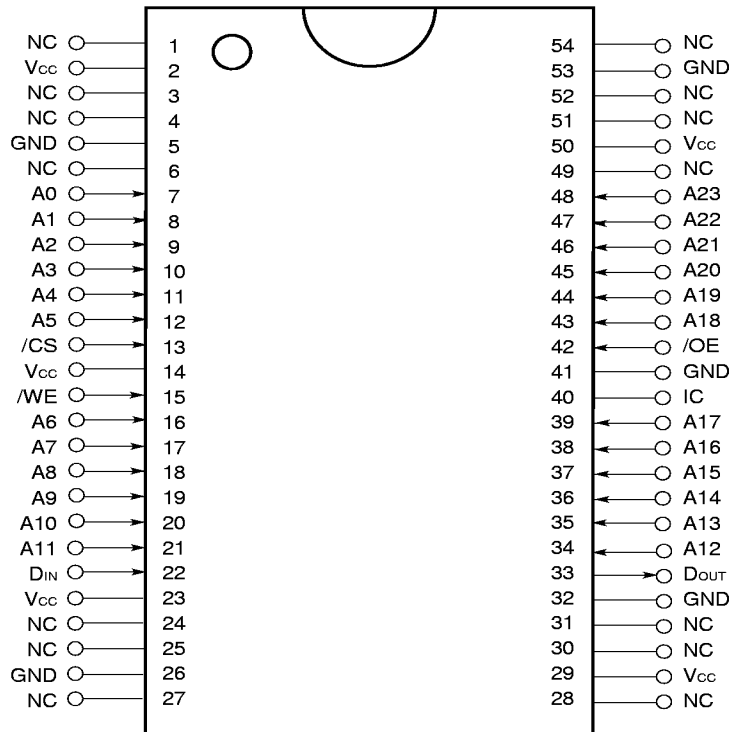
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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

Pin Configuration (Marking Side)

/xxx indicates active low signal.

54-pin plastic TSOP (II) (400 mil) (Normal bent)

[μPD4416001G5-xxx-9JF]

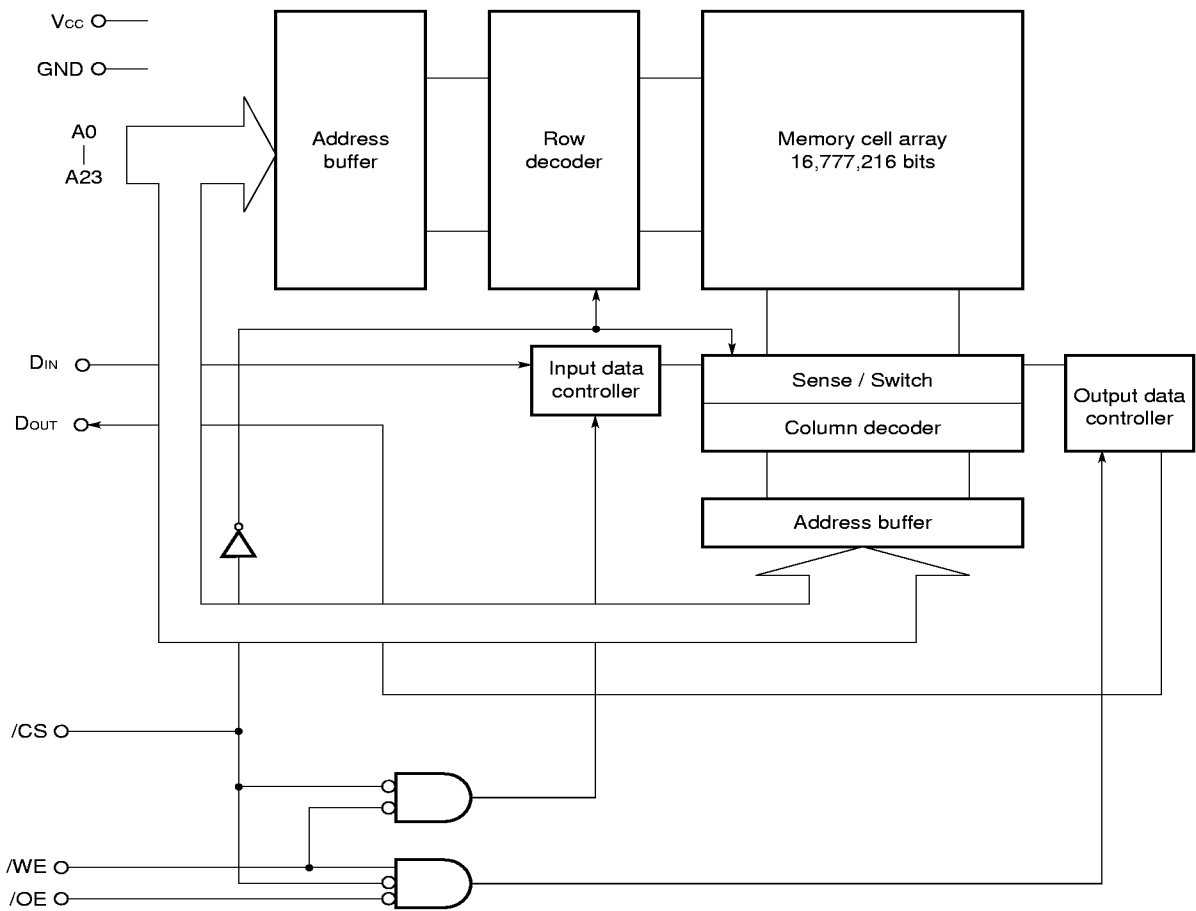


A0 - A23 : Address Inputs
DIn : Data Input
DOut : Data Output
/CS : Chip Select
/WE : Write Enable
/OE : Output Enable
Vcc : Power supply
GND : Ground
NC : No connection
IC : Internal connection ^{Note}

★

Note Leave this pin connect to GND.

Block Diagram



Truth Table

/CS	/OE	/WE	Mode	I/O	Supply current
H	×	×	Not selected	High impedance	I _{SB}
L	L	H	Read	D _{OUT}	I _{CC}
L	×	L	Write	D _{IN}	
L	H	H	Output disable	High impedance	

Remark × : Don't care

Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
★ Supply voltage	V _{CC}	A version	−0.5 ^{Note} to +4.6	V
		C version	−0.5 ^{Note} to +3.0	
★ Input / Output voltage	V _I	A version	−0.5 ^{Note} to +4.6	V
		C version	−0.5 ^{Note} to +3.0	
Operating ambient temperature	T _A		0 to +70	°C
Storage temperature	T _{stg}		−55 to +125	°C

Note −2.0 V (MIN.) (pulse width : 2 ns)

Caution Exposing the device to stress above those listed in Absolute Maximum Rating could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

(A version)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	V _{CC}		3.0	3.3	3.6	V
★ High level input voltage	V _{IH}		2.0		V _{CC} + 0.3	V
Low level input voltage	V _{IL}		−0.3 ^{Note}		+0.8	V
Operating ambient temperature	T _A		0		70	°C

Note −2.0 V (MIN.) (pulse width : 2 ns)

(C version)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	V _{CC}		2.375	2.5	2.625	V
High level input voltage	V _{IH}		1.7		V _{CC} + 0.3	V
Low level input voltage	V _{IL}		−0.3 ^{Note}		+0.7	V
Operating ambient temperature	T _A		0		70	°C

Note −2.0 V (MIN.) (pulse width : 2 ns)

DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

Parameter	Symbol	Test condition		MIN.	TYP.	MAX.	Unit
Input leakage current	I _{LI}	V _{IN} = 0 V to V _{CC}		−2		+2	μA
Output leakage current	I _{LO}	V _{OUT} = 0 V to V _{CC} , /CS = V _{IH} or /OE = V _{IH} or /WE = V _{IL}		−2		+2	μA
Operating supply current	I _{CC}	/CS = V _{IL} , I _{OUT} = 0 mA,	Cycle time : 12 ns			190	mA
		Minimum cycle time	Cycle time : 15 ns			150	
Standby supply current	I _{SB}	/CS = V _{IH} , V _{IN} = V _{IH} or V _{IL} , Minimum cycle time				80	mA
	I _{SB1}	V _{CC} − 0.2 V ≤ /CS, V _{IN} ≤ 0.2 V or V _{CC} − 0.2 V ≤ V _{IN}				10	
3.3 V LVTTTL Interface (A version)							
High level output voltage	V _{OH}	I _{OH} = −4.0 mA		2.4			V
Low level output voltage	V _{OL}	I _{OL} = +8.0 mA				0.4	V
2.5 V LVTTTL Interface (C version)							
High level output voltage	V _{OH}	I _{OH} = −2.0 mA		1.7			V
		I _{OH} = −1.0 mA		2.0			
Low level output voltage	V _{OL}	I _{OL} = +2.0 mA				0.7	V
		I _{OL} = +1.0 mA				0.4	

Remark V_{IN} : Input voltage, V_{OUT} : Output voltage

Capacitance ($T_A = 25\text{ }^\circ\text{C}$, $f = 1\text{ MHz}$)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	C_{IN}	$V_{IN} = 0\text{ V}$			6	pF
★ Input / Output capacitance	C_{OUT}	$V_{OUT} = 0\text{ V}$			8	pF

Remarks 1. V_{IN} : Input voltage, V_{OUT} : Output voltage

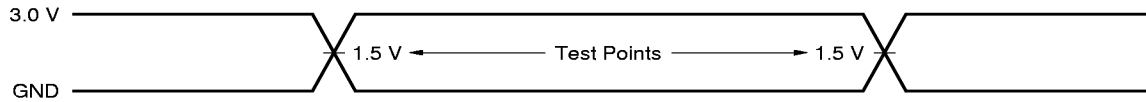
2. These parameters are periodically sampled and not 100% tested.

AC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

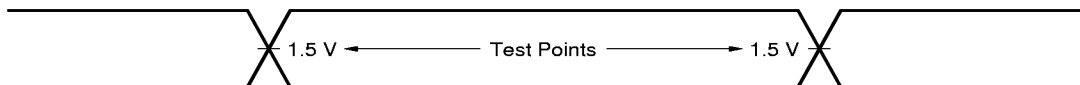
AC Test Conditions

3.3 V LVTTTL Interface (A version)

Input Waveform (Rise and Fall Time ≤ 3 ns)



Output Waveform



Output Load

AC characteristics directed with the note should be measured with the output load shown in Figure 1 or Figure 2.

Figure 1

(for t_{AA} , t_{ACS} , t_{OE} , t_{OH})

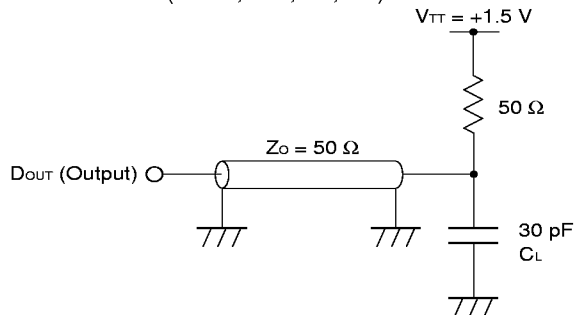
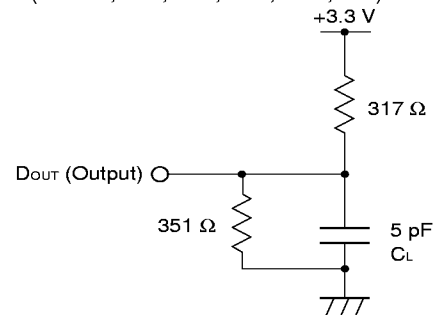


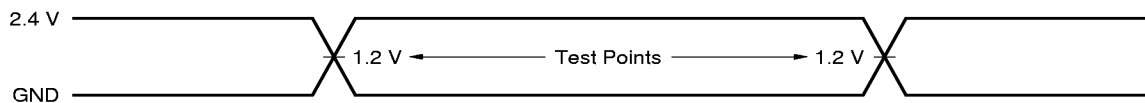
Figure 2

(for t_{CLZ} , t_{OLZ} , t_{CHZ} , t_{OHZ} , t_{WHZ} , t_{OW})

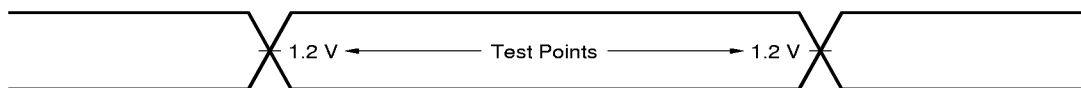


Remark C_L includes capacitances of the probe and jig, and stray capacitances.

2.5 V LVTTTL Interface (C version)

Input Waveform (Rise and Fall Time ≤ 2.4 ns)

Output Waveform



Output Load

AC characteristics directed with the note should be measured with the output load shown in Figure 1 or Figure 2.

★

Figure 3

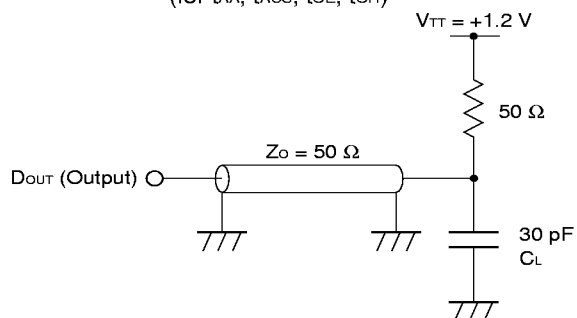
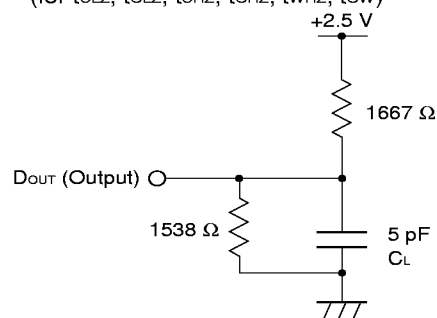
(for t_{AA} , t_{ACS} , t_{OE} , t_{OH})

Figure 4

(for t_{CLZ} , t_{OLZ} , t_{CHZ} , t_{OHZ} , t_{WHZ} , t_{OW})

Remark C_L includes capacitances of the probe and jig, and stray capacitances.

Read Cycle

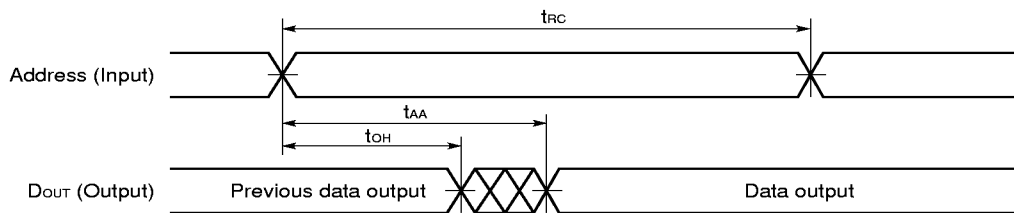
Parameter	Symbol	-A12		-A15		Unit	Notes
		MIN.	MAX.	MIN.	MAX.		
Read cycle time	t_{RC}	12		15		ns	
Address access time	t_{AA}		12		15	ns	1
/CS access time	t_{ACS}		12		15	ns	
/OE access time	t_{OE}		6		7	ns	
Output hold from address change	t_{OH}	3		3		ns	
/CS to output in low impedance	t_{CLZ}	3		3		ns	2, 3
/OE to output in low impedance	t_{OLZ}	0		0		ns	
/CS to output in high impedance	t_{CHZ}		6		7	ns	
/OE to output hold in high impedance	t_{OHZ}		6		7	ns	

Notes 1. See the output load shown in **Figure 1, 3**.

2. Transition is measured at ± 200 mV from steady-state voltage with the output load shown in **Figure 2, 4**.

3. These parameters are periodically sampled and not 100% tested.

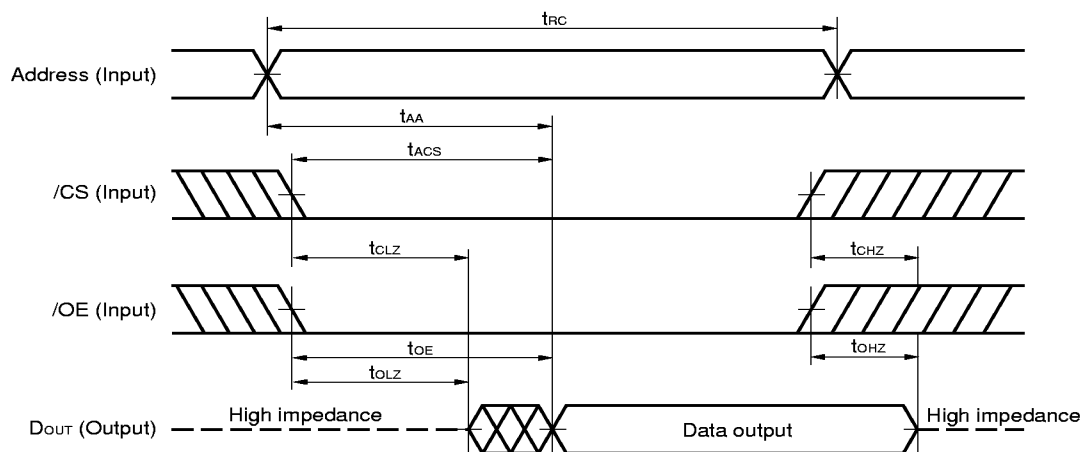
Read Cycle Timing Chart 1 (Address Access)



Remarks 1. In read cycle, /WE should be fixed to high level.

2. /CS = /OE = V_{IL}

Read Cycle Timing Chart 2 (/CS Access)



Caution Address valid prior to or coincident with /CS low level input.

Remark In read cycle, /WE should be fixed to high level.

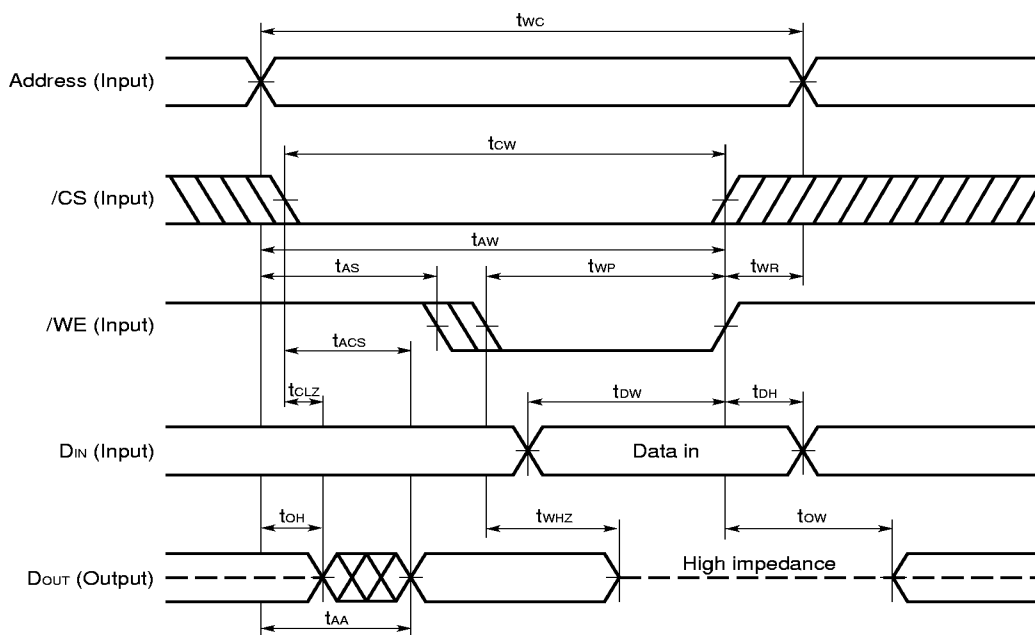
Write Cycle

Parameter	Symbol	-A12		-A15		Unit	Notes
		MIN.	MAX.	MIN.	MAX.		
Write cycle time	t_{WC}	12		15		ns	
/CS to end of write	t_{CW}	8		10		ns	
Address valid to end of write	t_{AW}	8		10		ns	
Write pulse width	t_{WP}	8		10		ns	
Data valid to end of write	t_{DW}	6		7		ns	
Data hold time	t_{DH}	0		0		ns	
Address setup time	t_{AS}	0		0		ns	
Write recovery time	t_{WR}	1		1		ns	
/WE to output in high impedance	t_{WHZ}		6		7	ns	1, 2
Output active from end of write	t_{OW}	3		3		ns	

Notes 1. Transition is measured at ± 200 mV from steady-state voltage with the output load shown in Figure 2, 4.

2. These parameters are periodically sampled and not 100% tested.

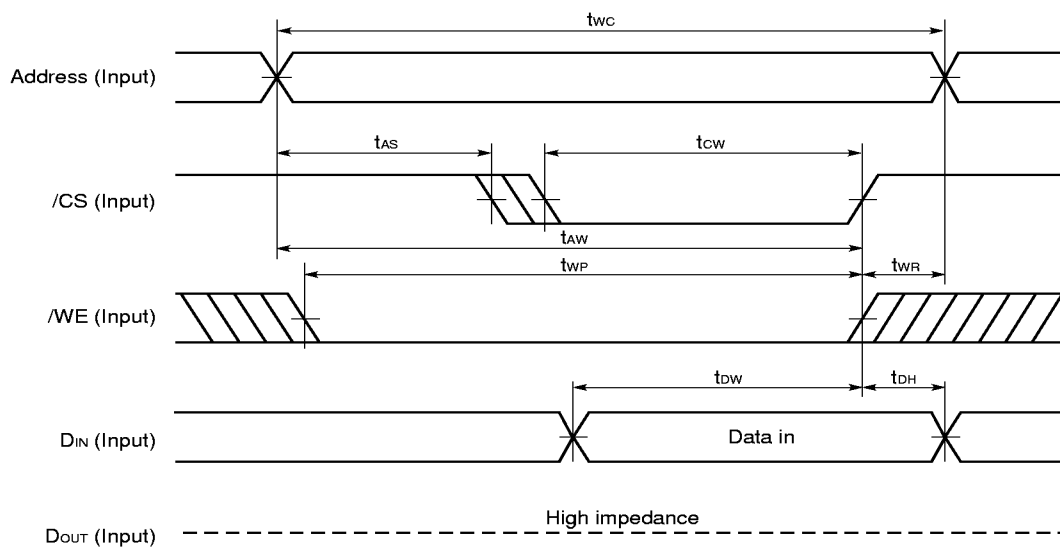
Write Cycle Timing Chart 1 (/WE Controlled)



Caution /CS or /WE should be fixed to high level during address transition.

- Remarks**
- Write operation is done during the overlap time of a low level /CS, a low level /WE.
 - During t_{WHZ} , DOUT pins are in the output state, therefore the input signals of opposite phase to the output must not be applied.
 - When /WE is at low level, the DOUT pins are always high impedance. When /WE is at high level, read operation is executed. Therefore /OE should be at high level to make the DOUT pins high impedance.

Write Cycle Timing Chart 2 (/CS Controlled)

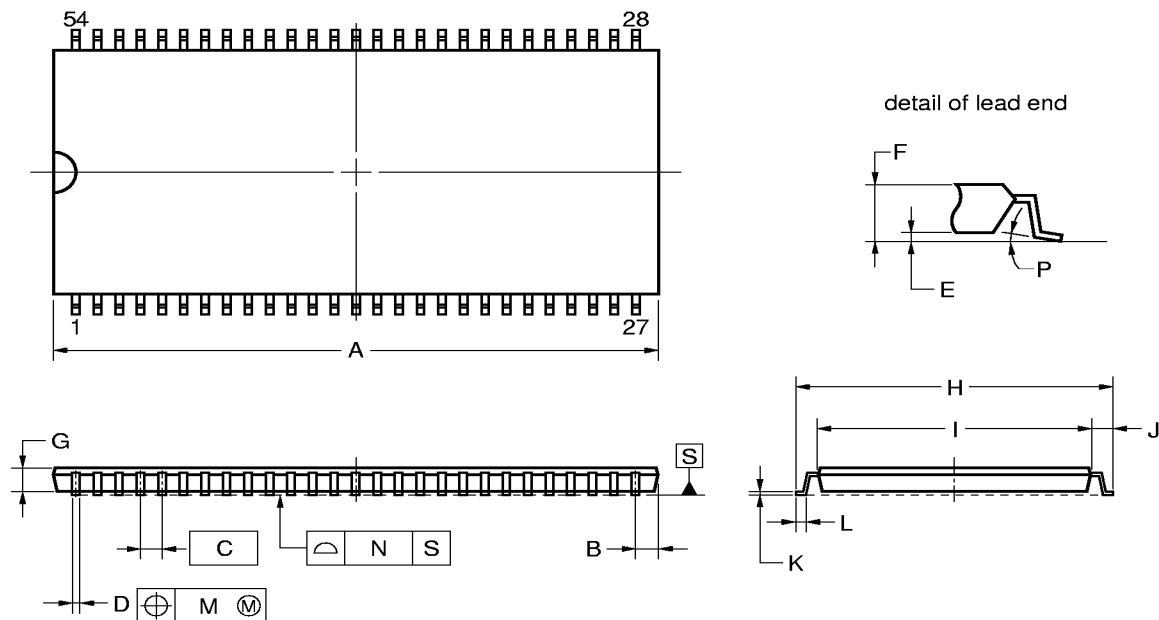


Caution /CS or /WE should be fixed to high level during address transition.

Remark Write operation is done during the overlap time of a low level /CS and a low level /WE.

Package Drawing

54PIN PLASTIC TSOP (II) (400mil)



NOTES

1. Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.
2. Dimension "A" does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per side.

ITEM	MILLIMETERS
A	22.22±0.05
B	0.91 MAX.
C	0.80 (T.P.)
D	0.32 ^{+0.08} _{-0.07}
E	0.10±0.05
F	1.1±0.1
G	1.00
H	11.76±0.20
I	10.16±0.10
J	0.80±0.20
K	0.145 ^{+0.025} _{-0.015}
L	0.50±0.10
M	0.13
N	0.10
P	3° ^{+7°} _{-3°}

S54G5-80-9JF-1